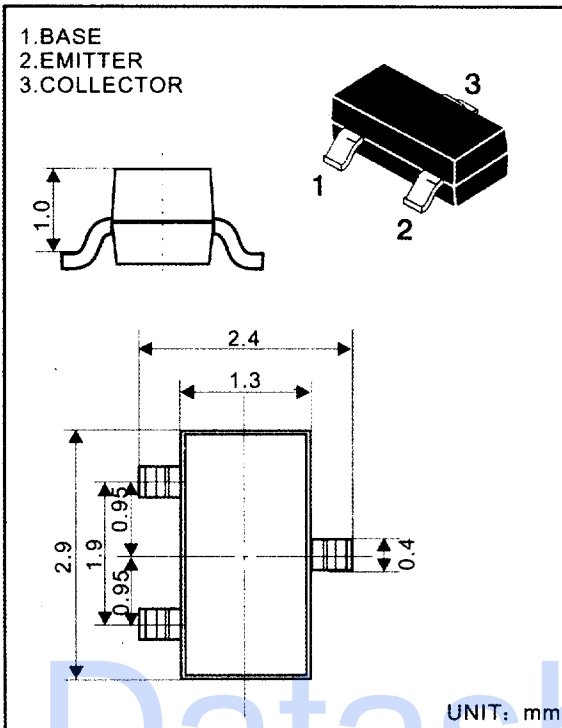


SOT-23 Plastic-Encapsulate Transistors

MMBT2222ALT1 TRANSISTOR (NPN)



FEATURES

Power dissipation

P_{CM} : 0.3 W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : 0.6 A

Collector-base voltage

$V_{(BR)CBO}$: 75V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

ELECTRICAL CHARACTERISTICS

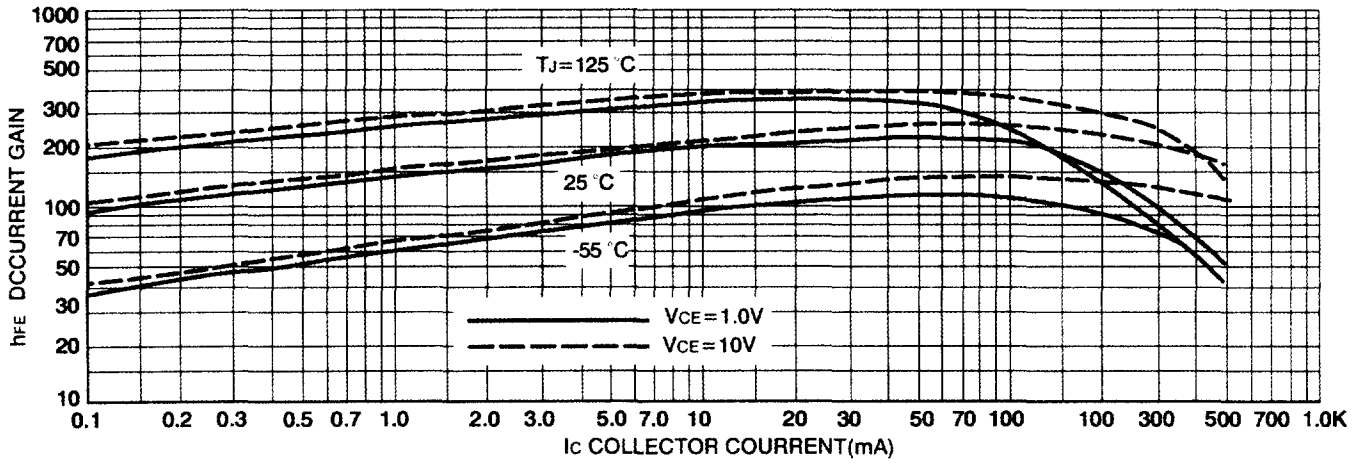
($T_{amp}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=10\mu A, I_E=0$	75		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=10mA, I_B=0$	40		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu A, I_B=0$	6		V
Collector cut-off current	I_{CBO}	$V_{CB}=70V, I_E=0$		0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE}=35V, I_B=0$		0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=3V, I_C=0mA$		0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=10V, I_C=150mA$	100	300	
	$h_{FE(2)}$	$V_{CE}=10V, I_C=1mA$	50		
Collector-emitter saturation voltage	V_{CEsat}	$I_C=500mA, I_B=50mA$		1	V
Base-emitter saturation voltage	V_{BEsat}	$I_C=500mA, I_B=50mA$		2	V
Transition frequency	f_T	$V_{CE}=20V, I_C=20mA, f=100MHz$	300		MHz

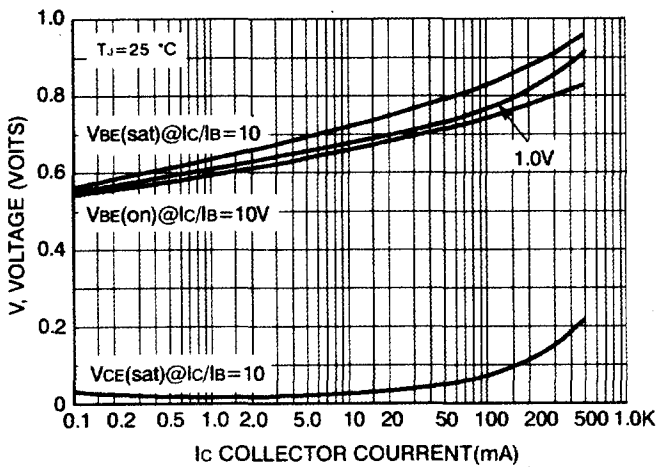
DEVICE MARKING : MMBT2222ALT1=1P

Typical Characteristics

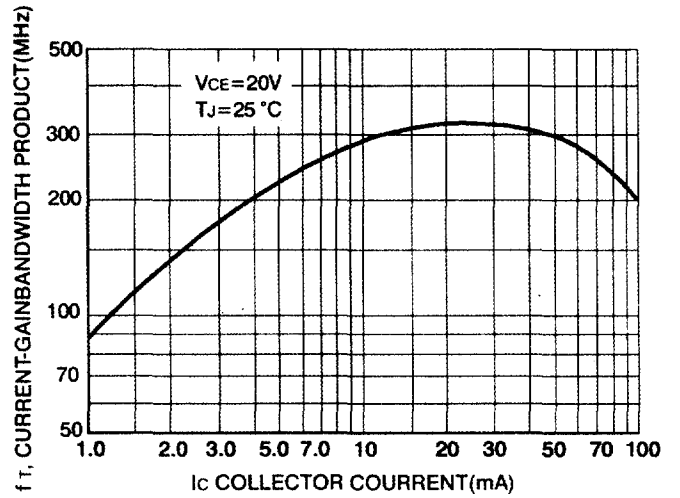
MMBT2222ALT1



DC Current Gain



"On" Voltages



Current-Gain Bandwidth Product